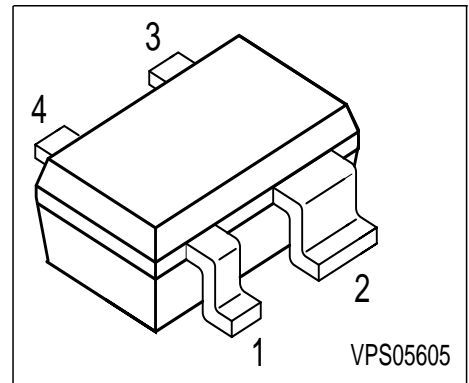


**NPN Silicon RF Transistor**

- For power amplifier in DECT and PCN systems
- $f_T = 5.5\text{GHz}$
- Gold metalization for high reliability



**ESD: Electrostatic discharge sensitive device, observe handling precaution!**

Type	Marking	Pin Configuration				Package
BFP136W	PAs	1 = E	2 = C	3 = E	4 = B	SOT343

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$	12	V
Collector-emitter voltage	$V_{CES}$	20	
Collector-base voltage	$V_{CBO}$	20	
Emitter-base voltage	$V_{EBO}$	2	
Collector current	$I_C$	150	mA
Base current	$I_B$	20	
Total power dissipation $T_S \leq 60^\circ\text{C}^1)$	$P_{tot}$	1000	mW
Junction temperature	$T_j$	150	°C
Ambient temperature	$T_A$	-65 ... 150	
Storage temperature	$T_{stg}$	-65 ... 150	

**Thermal Resistance**

Junction - soldering point <sup>2)</sup>	$R_{thJS}$	$\leq 90$	K/W
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<sup>1</sup>  $T_S$  is measured on the collector lead at the soldering point to the pcb

<sup>2</sup> For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC characteristics</b>					
Collector-emitter breakdown voltage $I_C = 1 \text{ mA}, I_B = 0$	$V_{(BR)CEO}$	12	-	-	V
Collector-emitter cutoff current $V_{CE} = 20 \text{ V}, V_{BE} = 0$	$I_{CES}$	-	-	100	$\mu\text{A}$
Collector-base cutoff current $V_{CB} = 10 \text{ V}, I_E = 0$	$I_{CBO}$	-	-	50	nA
Emitter-base cutoff current $V_{EB} = 1 \text{ V}, I_C = 0$	$I_{EBO}$	-	-	1	$\mu\text{A}$
DC current gain $I_C = 80 \text{ mA}, V_{CE} = 5 \text{ V}$	$h_{FE}$	50	100	200	-

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>AC characteristics</b> (verified by random sampling)					
Transition frequency $I_C = 80\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $f = 500\text{ MHz}$	$f_T$	4	5.5	-	GHz
Collector-base capacitance $V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$	$C_{cb}$	-	1.7	2.5	pF
Collector-emitter capacitance $V_{CE} = 10\text{ V}$ , $f = 1\text{ MHz}$	$C_{ce}$	-	0.7	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$ , $f = 1\text{ MHz}$	$C_{eb}$	-	6.8	-	
Noise figure $I_C = 30\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $Z_S = Z_{Sopt}$ , $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	$F$	-	2 3.3	-	dB
Power gain, maximum available <sup>1)</sup> $I_C = 80\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $Z_S = Z_{Sopt}$ , $Z_L = Z_{Lopt}$ , $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	$G_{ma}$	-	15.5 9.5	-	
Transducer gain $I_C = 80\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $Z_S = Z_L = 50\Omega$ , $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	$ S_{21e} ^2$	-	9 3	-	
Third order intercept point $I_C = 80\text{ mA}$ , $V_{CE} = 5\text{ V}$ , $Z_S = Z_{Sopt}$ , $Z_L = Z_{Lopt}$ , $f = 1.8\text{ GHz}$	$IP_3$	-	33	-	dBm

$$^1G_{ma} = |S_{21} / S_{12}| (k - (k^2 - 1)^{1/2})$$

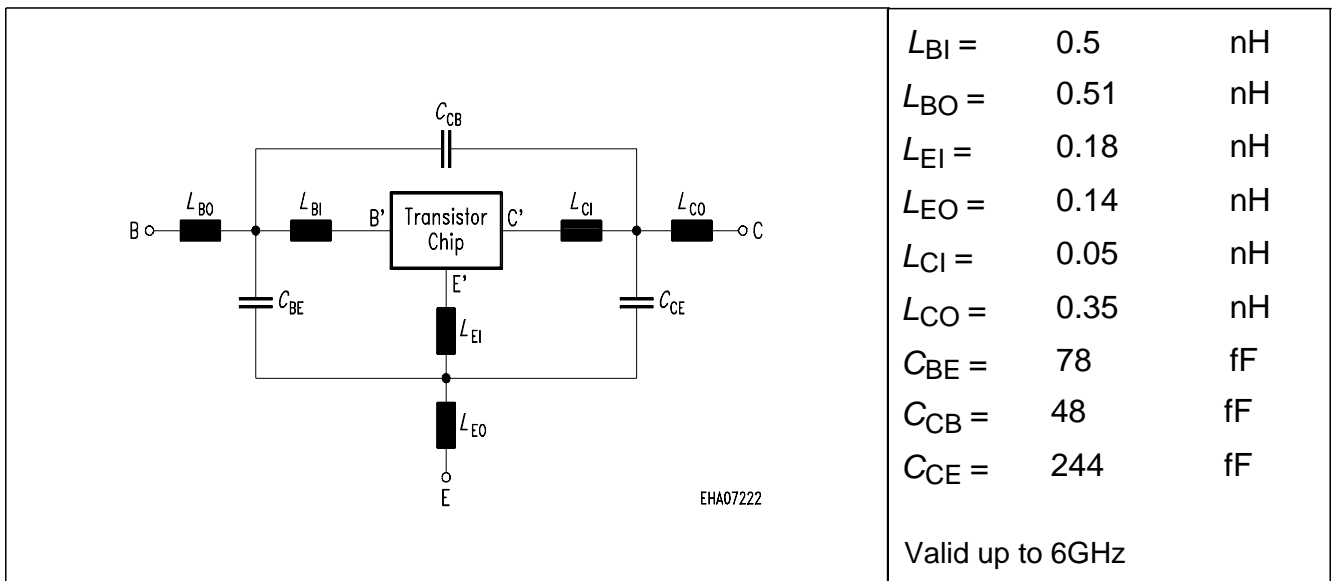
**SPICE Parameters (Gummel-Poon Model, Berkley-SPICE 2G.6 Syntax) :**

**Transistor Chip Data**

IS =	1.5813	fA	BF =	113.32	-	NF =	1.0653	-
VAF =	12.331	V	IKF =	1.4907	A	ISE =	46.37	fA
NE =	1.4254	-	BR =	86.717	-	NR =	1.8047	-
VAR =	31.901	V	IKR =	0.033605	A	ISC =	0.0080864	fA
NC =	1.8821	-	RB =	0	$\Omega$	IRB =	0.83992	mA
RBM =	1.0078	$\Omega$	RE =	0.22081	$\Omega$	RC =	0.01636	$\Omega$
CJE =	33.904	fF	VJE =	0.71518	V	MJE =	0.36824	-
TF =	20.691	ps	XTF =	0.31338	-	VTF =	0.10174	V
ITF =	4.5579	mA	PTF =	0	deg	CJC =	2977.4	fF
VJC =	1.1381	V	MJC =	0.31461	-	XCJC =	0.02899	-
TR =	1.0033	ns	CJS =	0	fF	VJS =	0.75	V
MJS =	0	-	XTB =	0	-	EG =	1.11	eV
XTI =	3	-	FC =	0.99886	-	TNOM	300	K

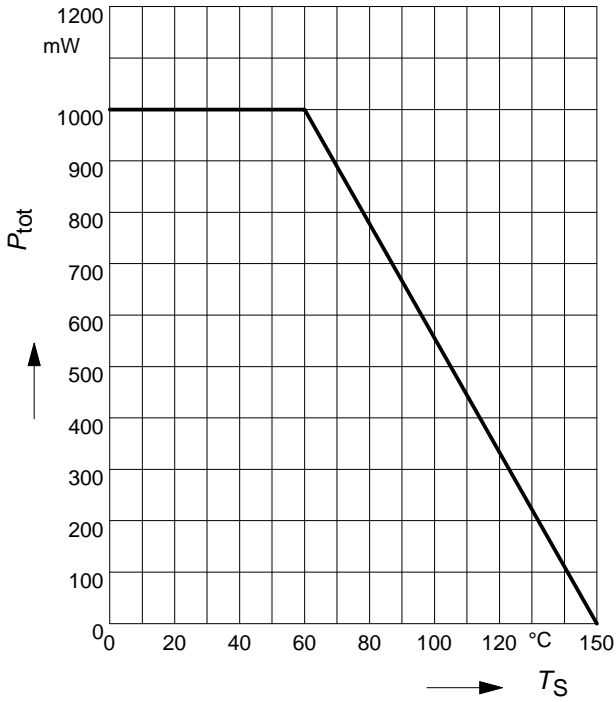
All parameters are ready to use, no scaling is necessary.  
 Extracted on behalf of Infineon Technologies AG by:  
 Institut für Mobil-und Satellitentechnik (IMST)

**Package Equivalent Circuit:**

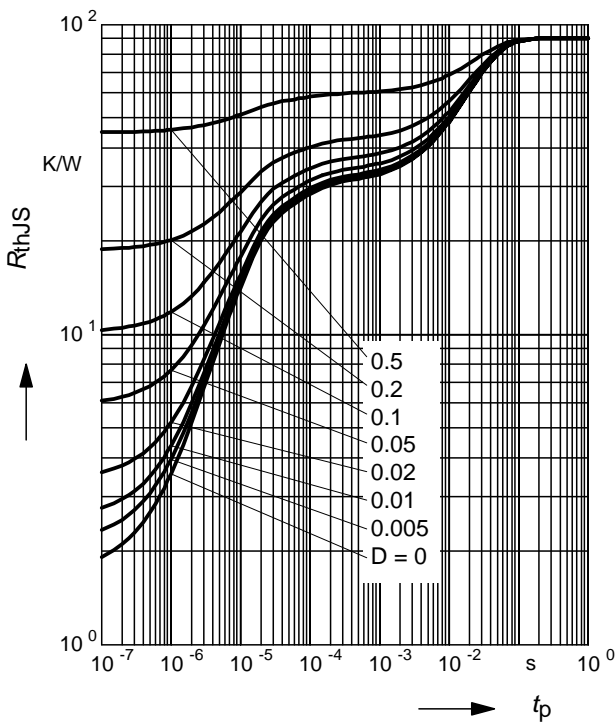


For examples and ready to use parameters please contact your local Infineon Technologies distributor or sales office to obtain a Infineon Technologies CD-ROM or see Internet: <http://www.infineon.com/products/discrete/index.htm>

**Total power dissipation  $P_{tot} = f(T_S)$**

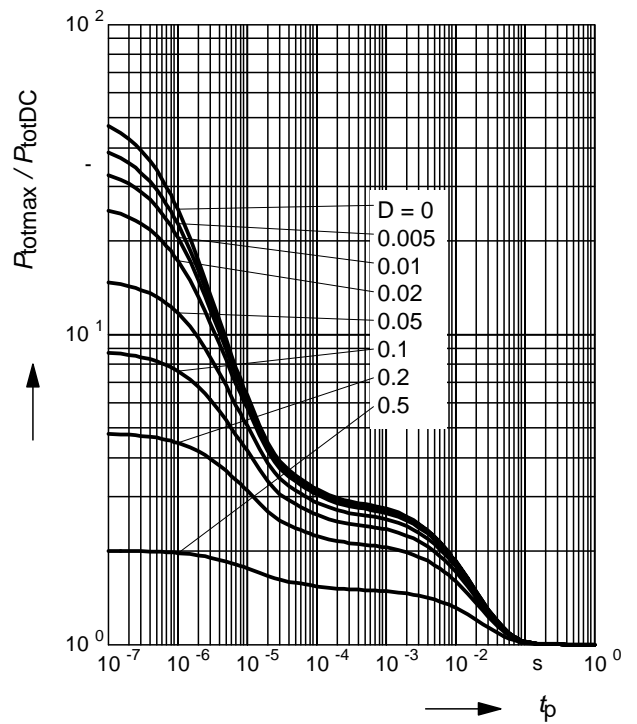


**Permissible Pulse Load  $R_{thJS} = f(t_p)$**



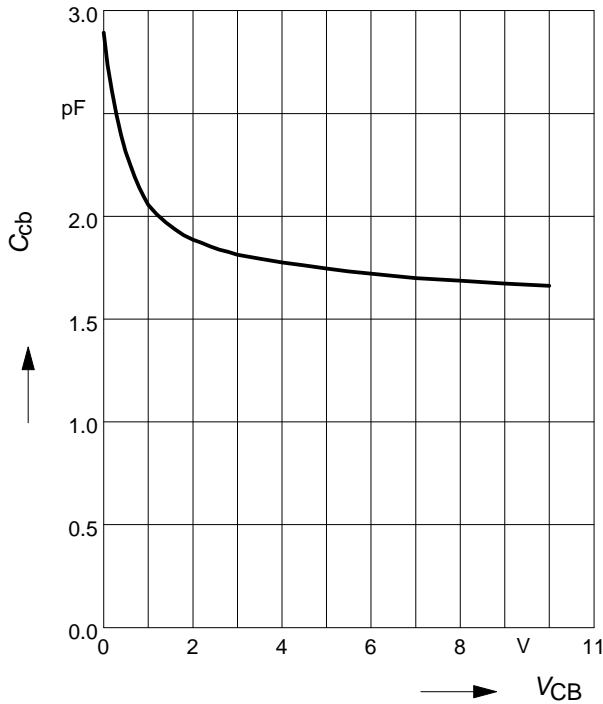
**Permissible Pulse Load**

$P_{totmax} / P_{totDC} = f(t_p)$



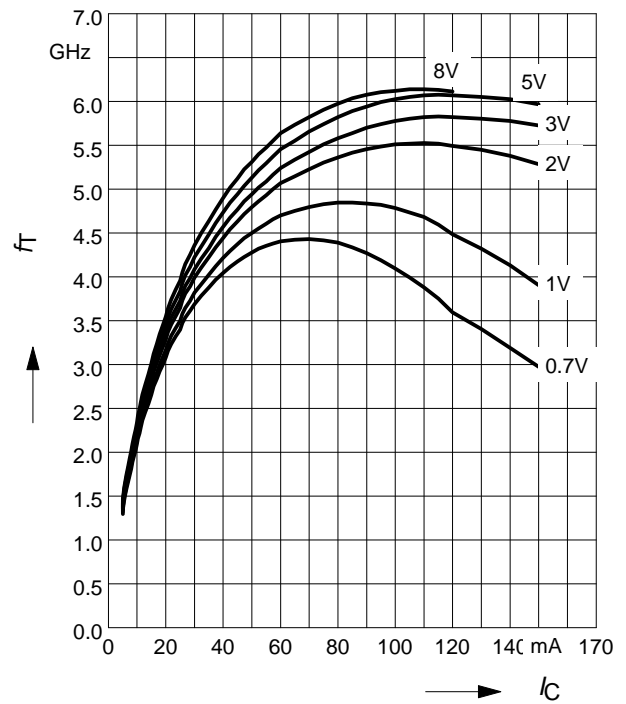
**Collector-base capacitance  $C_{cb} = f(V_{CB})$**

$f = 1\text{MHz}$



**Transition frequency  $f_T = f(I_C)$**

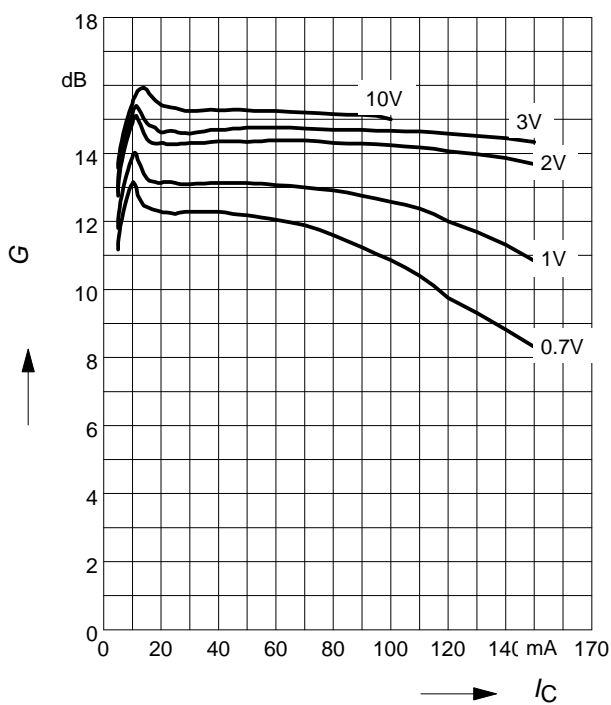
$V_{CE} = \text{Parameter}$



**Power Gain  $G_{ma}, G_{ms} = f(I_C)$**

$f = 0.9\text{GHz}$

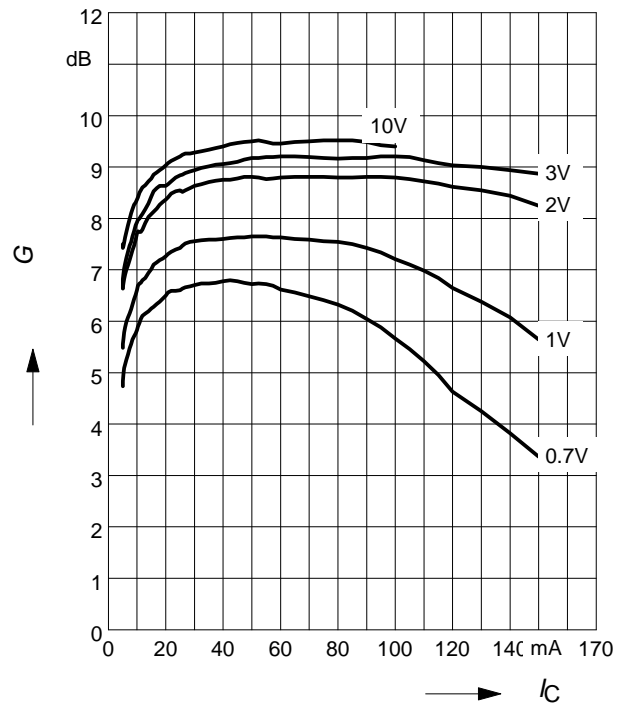
$V_{CE} = \text{Parameter}$



**Power Gain  $G_{ma}, G_{ms} = f(I_C)$**

$f = 1.8\text{GHz}$

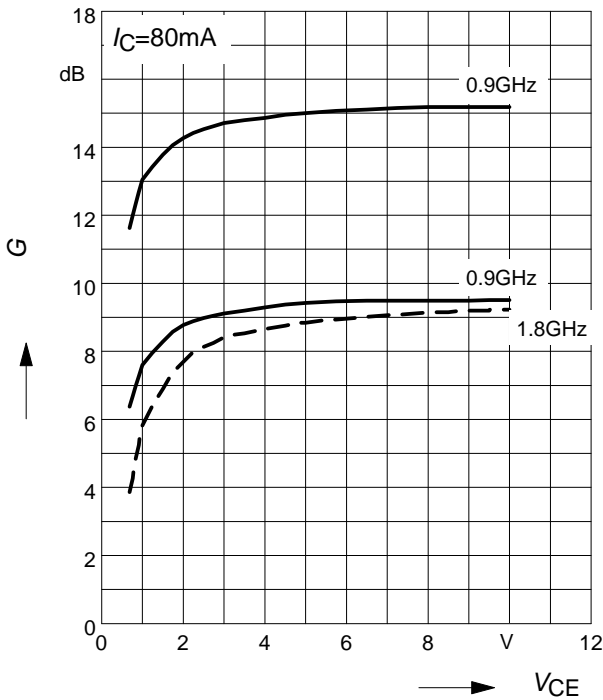
$V_{CE} = \text{Parameter}$



**Power Gain**  $G_{ma}, G_{ms} = f(V_{CE})$ : \_\_\_\_\_

$|S_{21}|^2 = f(V_{CE})$ : -----

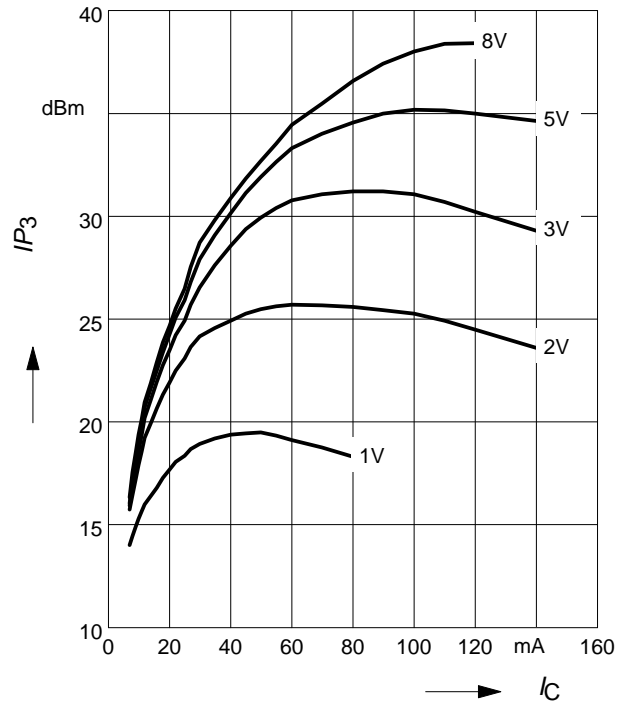
$f =$  Parameter



**Intermodulation Intercept Point**  $IP_3 = f(I_C)$

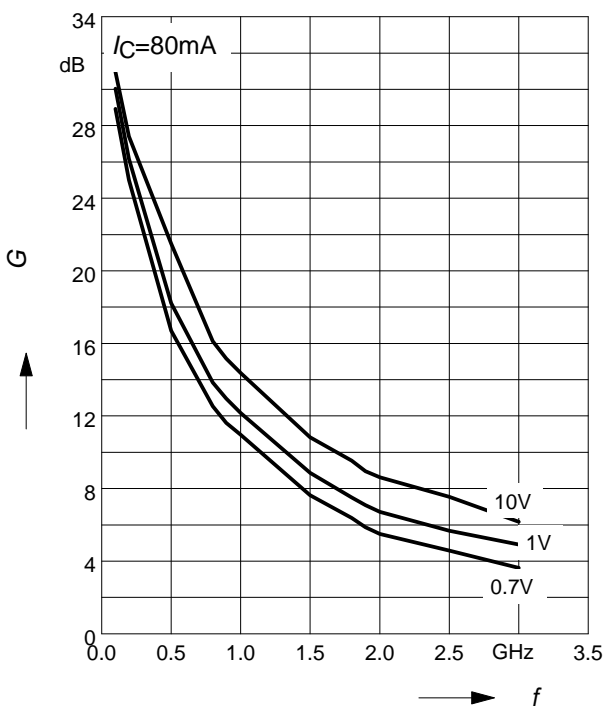
(3rd order, Output,  $Z_S = Z_L = 50\Omega$ )

$V_{CE} =$  Parameter,  $f = 900\text{MHz}$



**Power Gain**  $G_{ma}, G_{ms} = f(f)$

$V_{CE} =$  Parameter



**Power Gain**  $|S_{21}|^2 = f(f)$

$V_{CE} =$  Parameter

